General Description

The WSD20L50DN is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSD20L50DN meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

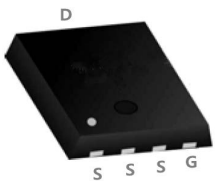
Product Summery

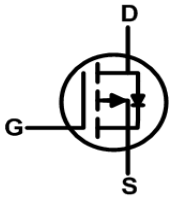
BVDSS	RDSON	ID
-20V	9.0mΩ	-50A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN3.3x3.3A-8_EP Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	-20		V
V_{GS}	Gate-Source Voltage	±12		V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-50		A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ -10V[1]	-22		A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ -10V[1]	-13.5	-10	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ -10V[1]	-10.5	-8.0	A
I_{DM}	Pulsed Drain Current[2]	-70		A
EAS	Single Pulse Avalanche Energy[3]	36		mJ
I_{AS}	Avalanche Current	-12		A
P_D@T_C=25℃	Total Power Dissipation[4]	31.25		W
P_D@T_A=25℃	Total Power Dissipation[4]	3.1	2.0	W
T_{STG}	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	80	℃/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1] (t ≤10s)	---	40	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	4.0	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-20	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BVDSS Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.0232	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-4.5V , I_D=-10A	---	9	11	mΩ
		V_{GS}=-2.5V , I_D=-8A	---	11	15	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-0.5	---	-1.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-16V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-16V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-10A	---	13	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	9	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-10V , V_{GS}=-4.5V , I_D=-11A	---	25	---	nC
Q_{gs}	Gate-Source Charge		---	1.6	---	
Q_{gd}	Gate-Drain Charge		---	11	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-10V , V_{GS}=-4.5V , R_G=6Ω I_D=-1A ,R_L=15Ω	---	9	---	ns
T_r	Rise Time		---	13	---	
$T_{d(off)}$	Turn-Off Delay Time		---	26	---	
T_f	Fall Time		---	167	---	
C_{iss}	Input Capacitance	V_{DS}=-10V , V_{GS}=0V , f=1MHz	---	1620	---	pF
C_{oss}	Output Capacitance		---	320	---	
C_{rss}	Reverse Transfer Capacitance		---	290	---	

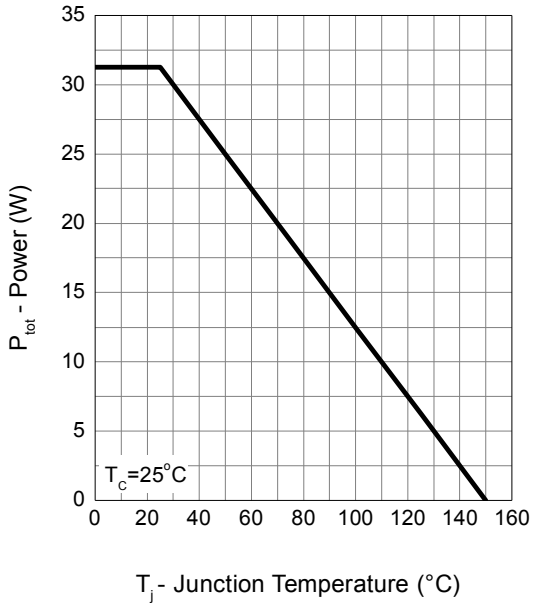
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	V_G=V_D=0V , Force Current	---	---	-10	A
I_{SM}	Pulsed Source Current[2,6]		---	---	-40	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V
t_{rr}	Reverse Recovery Time	IF=-20A,dI/dt=100A/μs, T_J=25℃	---	63	---	nS
Q_{rr}	Reverse Recovery Charge		---	54	---	nC

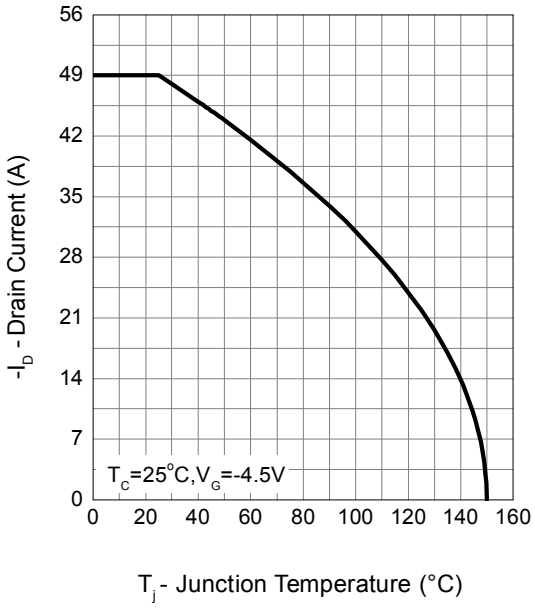
Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t≦10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.5mH,I_{AS}=-18A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

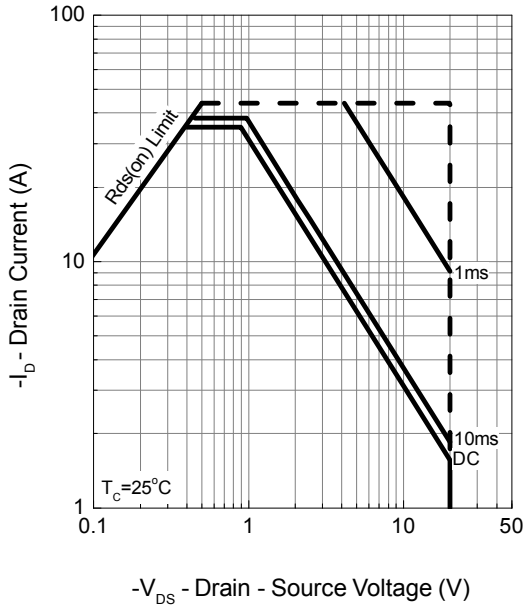
Power Dissipation



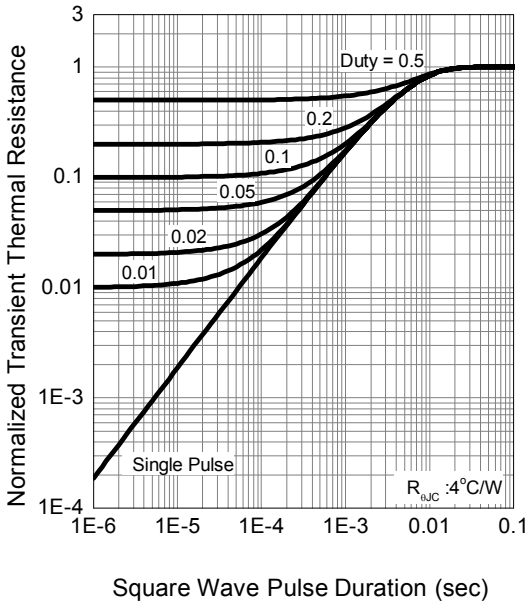
Drain Current



Safe Operation Area

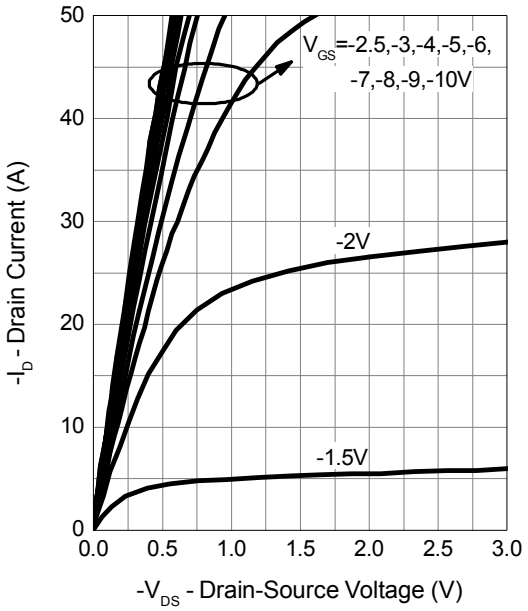


Thermal Transient Impedance

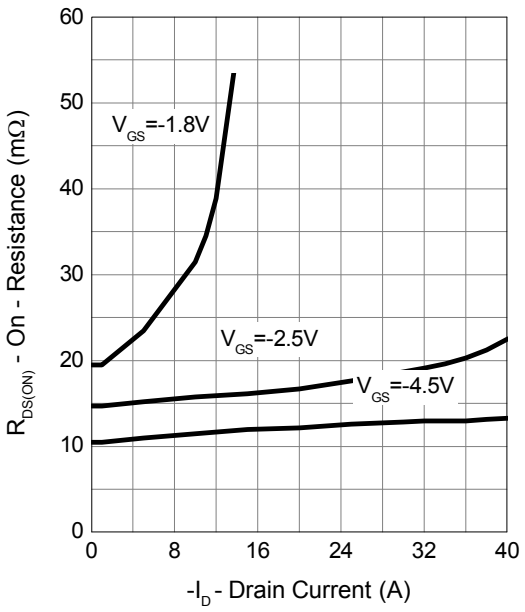


Typical Characteristics

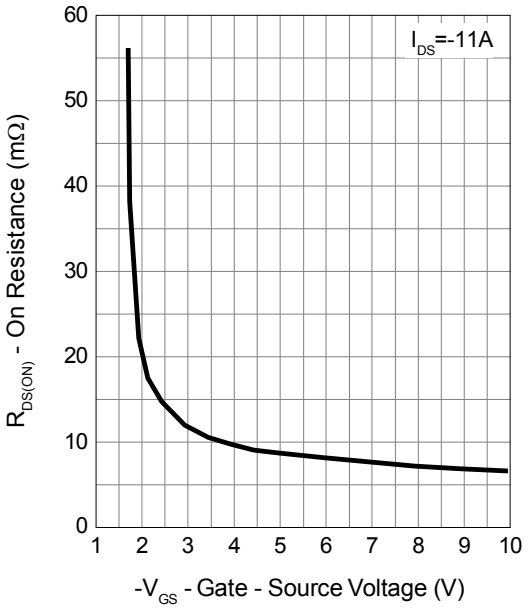
Output Characteristics



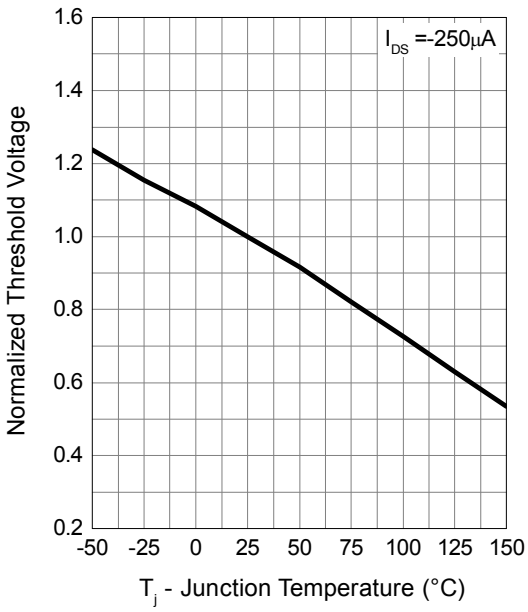
Drain-Source On Resistance



Gate-Source On Resistance

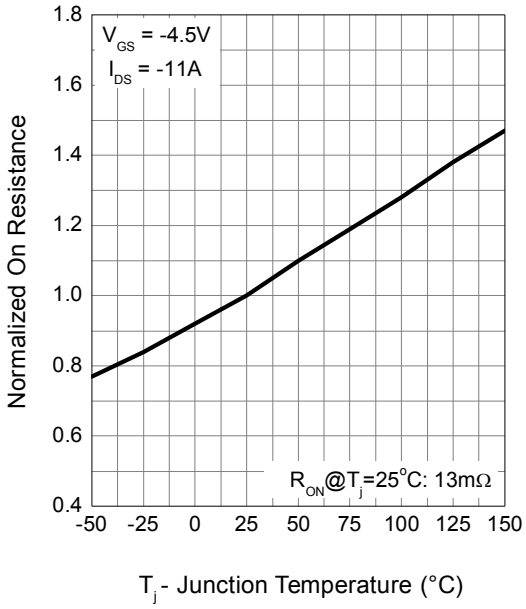


Gate Threshold Voltage

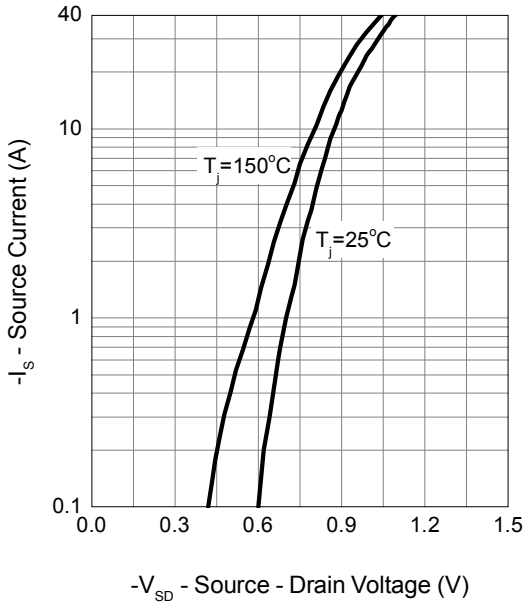


Typical Characteristics

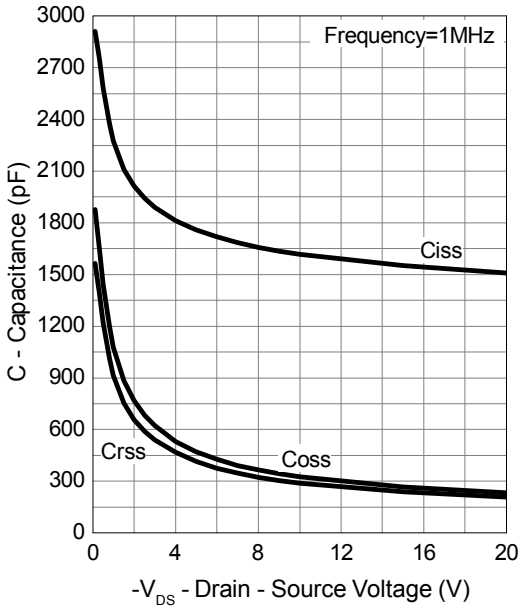
Drain-Source On Resistance



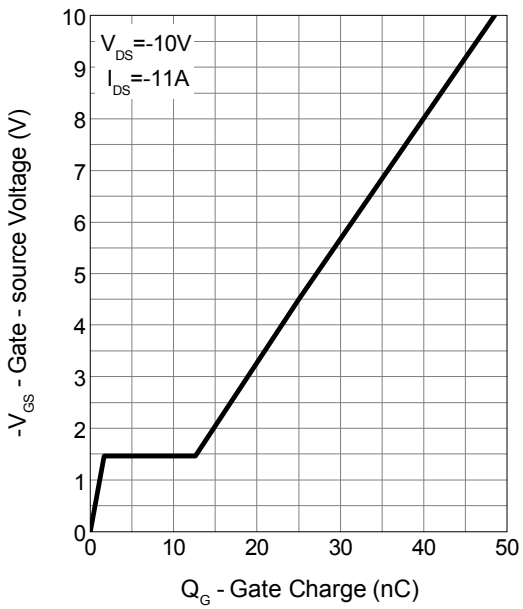
Source-Drain Diode Forward



Capacitance

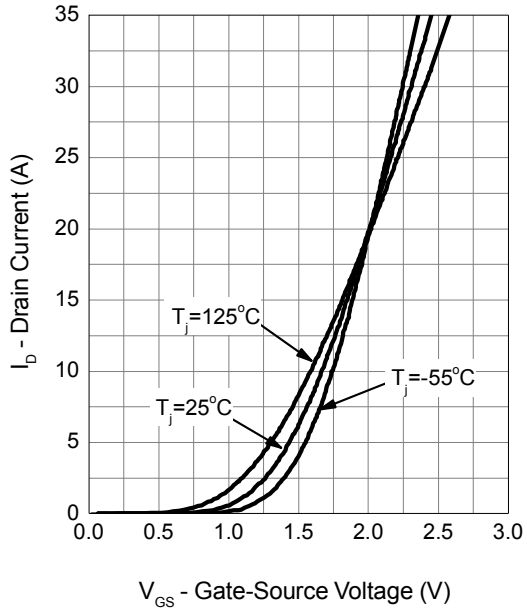


Gate Charge



Typical Characteristics

Transfer Characteristics



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